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STB120N4F6 STD120N4F6

N-channel 40 V, 3.5 mΩ, 80 A, DPAK, D²PAK
 STripFET™ VI DeepGATE™ Power MOSFET

Features

Order codes	V _{DSS}	R _{DS(on)} max.	I _D
STB120N4F6	40 V	4 mΩ	80 A ⁽¹⁾
STD120N4F6	40 V	4 mΩ	80 A ⁽¹⁾

1. Current limited by package

- Standard threshold drive
- 100% avalanche tested

Application

- Switching applications
- Automotive

Description

These devices are 40 V N-channel STripFET™ VI Power MOSFET based on the ST's proprietary STripFET™ technology, with a new gate structure. The resulting Power MOSFET exhibits the lowest R_{DS(on)} in all packages.

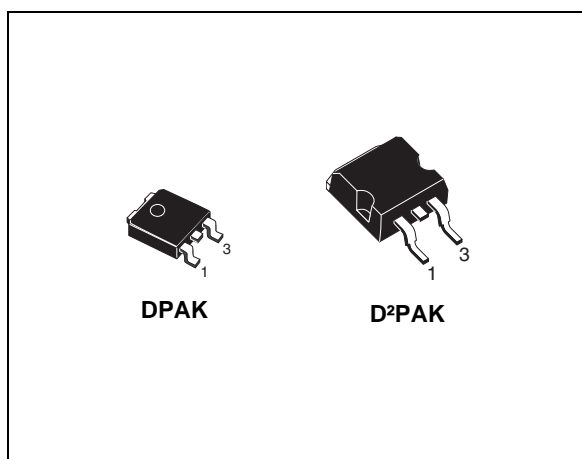
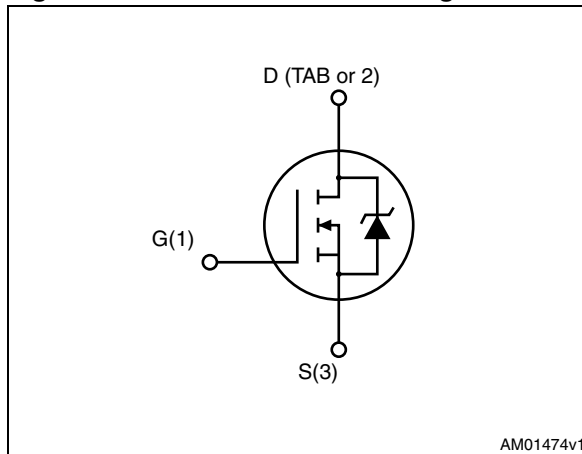


Figure 1. Internal schematic diagram



AM01474v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB120N4F6	120N4F6	D ² PAK	Tape and reel
STD120N4F6		DPAK	

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	40	V
V_{GS}	Gate-source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
T_{stg}	Storage temperature	-55 to 175	$^\circ\text{C}$
T_j	Operating junction temperature		

1. Current limited by package
2. Pulse width limited by safe operating area

Table 3. Thermal resistance

Symbol	Parameter	Value		Unit
		DPAK	D ² PAK	
$R_{thj-case}$	Thermal resistance junction-case max	1.36		$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max ⁽¹⁾	50	35	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² 2 oz. Cu board.

Table 4. Thermal resistance

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not-repetitive	40	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	394	mJ

1. Pulse width limited by T_j max
2. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 40\text{ A}$, $V_{DD} = 25\text{ V}$

Electrical characteristics

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2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown Voltage	I _D = 250 μA, V _{GS} = 0	40			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = 20 V V _{DS} = 20 V, T _c = 125 °C			1 10	μA μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	2		4	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 40 A		3.5	4.0	mΩ

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 25 V, f=1 MHz, V _{GS} = 0 V	-	3850	-	pF
C _{oss}	Output capacitance			650		pF
C _{rss}	Reverse transfer capacitance			350		pF
Q _g	Total gate charge	V _{DD} = 20 V, I _D = 80 A	-	65	-	nC
Q _{gs}	Gate-source charge	V _{GS} = 10 V		20		nC
Q _{gd}	Gate-drain charge	(see Figure 14)		16		nC
R _G	Intrinsic gate resistance	f = 1 MHz open drain	-	1.5	-	Ω

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Electrical characteristics
Table 7. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 20\text{ V}$, $I_D = 40\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ <i>(see Figure 15)</i>	-	20	-	ns
t_r	Rise time		-	70	-	ns
$t_{d(off)}$	Turn-off delay time	<i>(see Figure 15)</i>	-	40	-	ns
t_f	Fall time		-	20	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40\text{ A}$, $V_{GS} = 0$	-		1.1	V
t_{rr}	Reverse recovery time	$I_{SD} = 80\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 30\text{ V}$ <i>(see Figure 17)</i>	-	40		ns
Q_{rr}	Reverse recovery charge		-	56		nC
I_{RRM}	Reverse recovery current		-	2.8		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Electrical characteristics

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2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

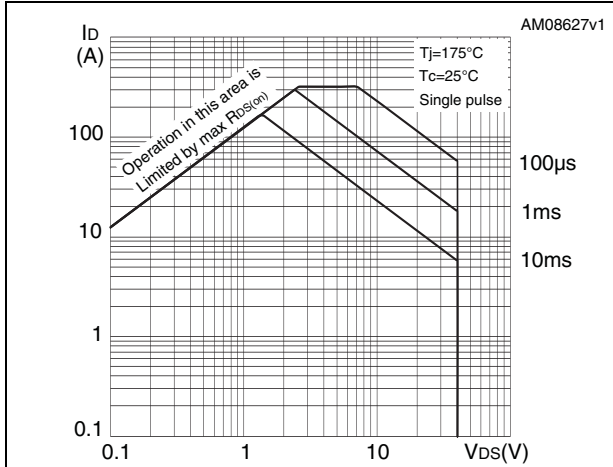


Figure 3. Thermal impedance

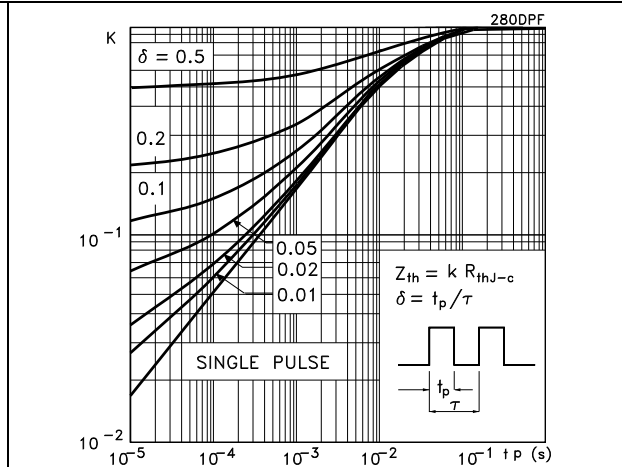


Figure 4. Output characteristics

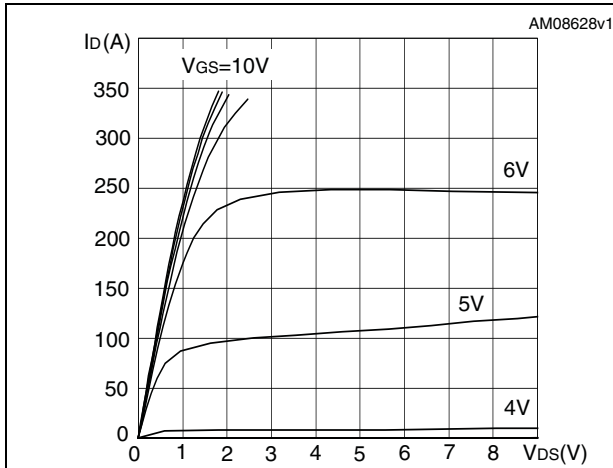


Figure 5. Transfer characteristics

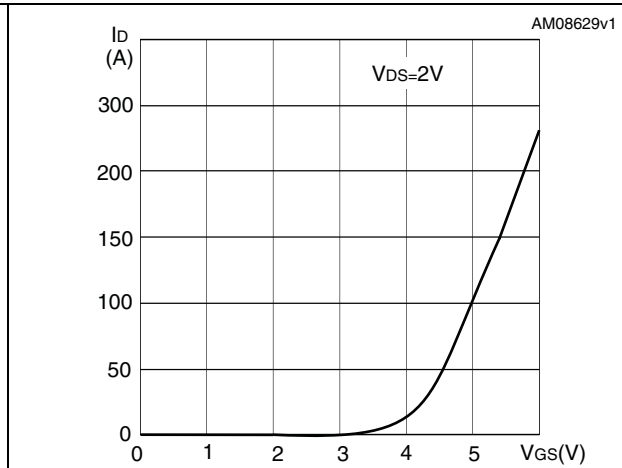


Figure 6. Normalized BVdss vs temperature

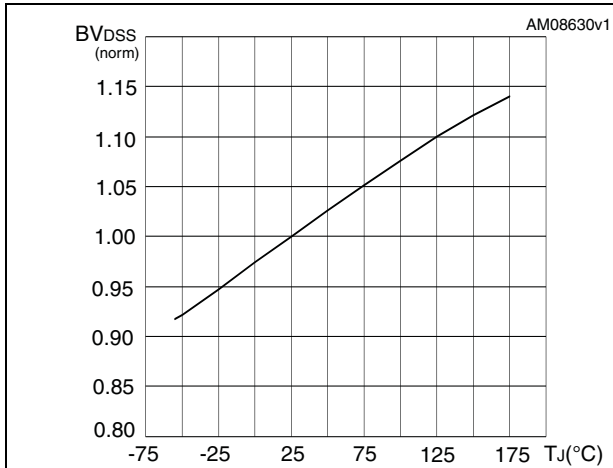
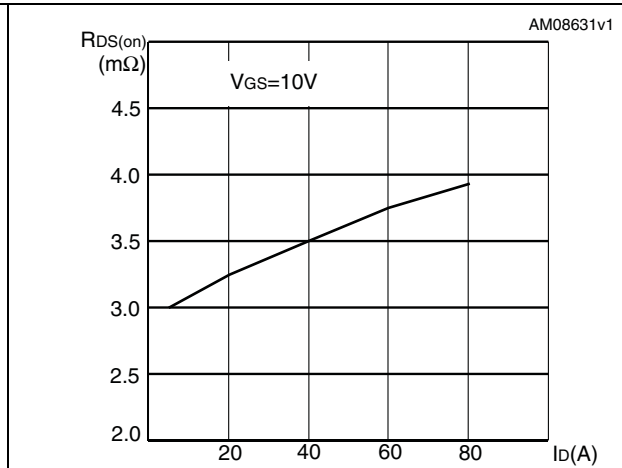


Figure 7. Static drain-source on resistance



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Electrical characteristics

Figure 8. Gate charge vs gate-source voltage **Figure 9. Capacitance variations**

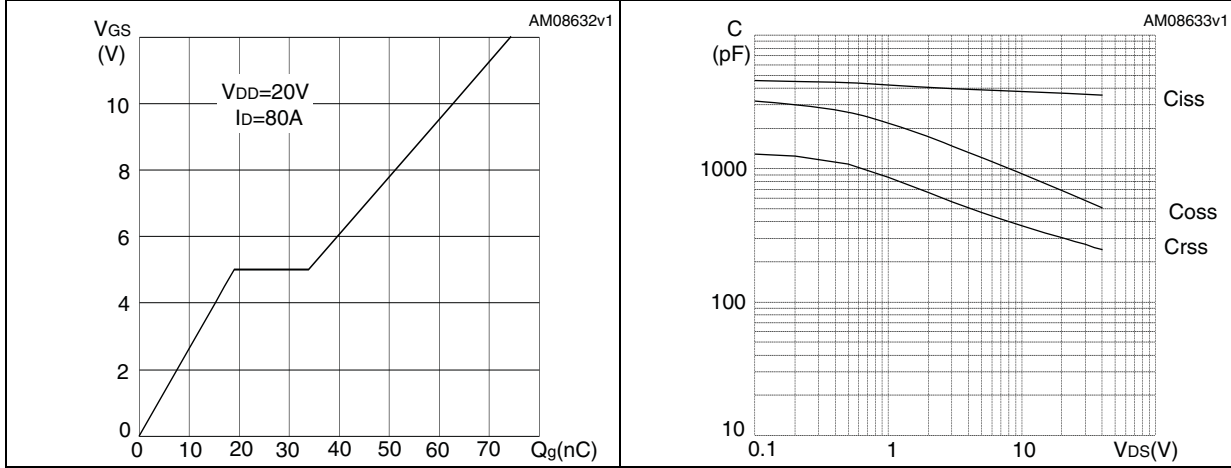


Figure 10. Normalized gate threshold voltage vs temperature **Figure 11. Normalized on resistance vs temperature**

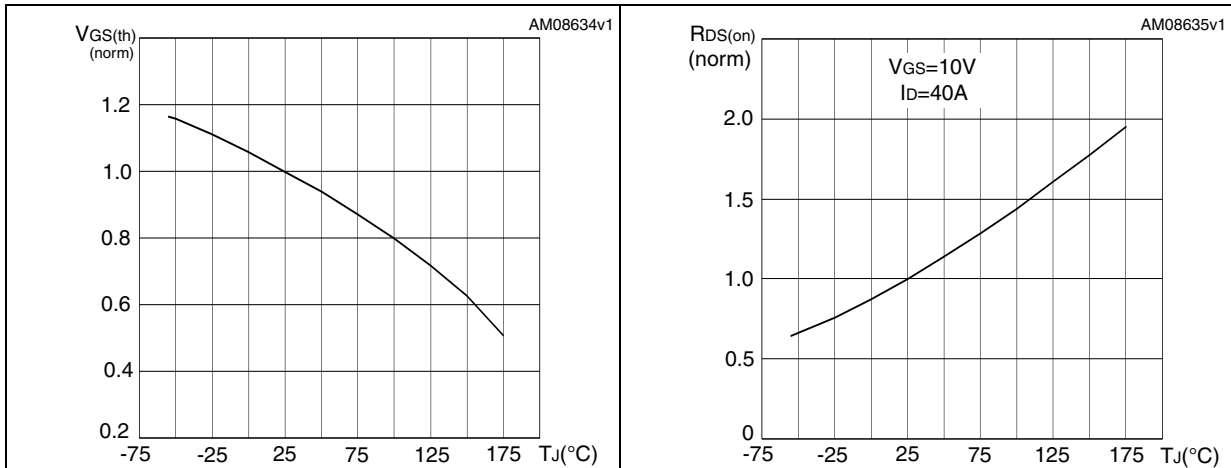
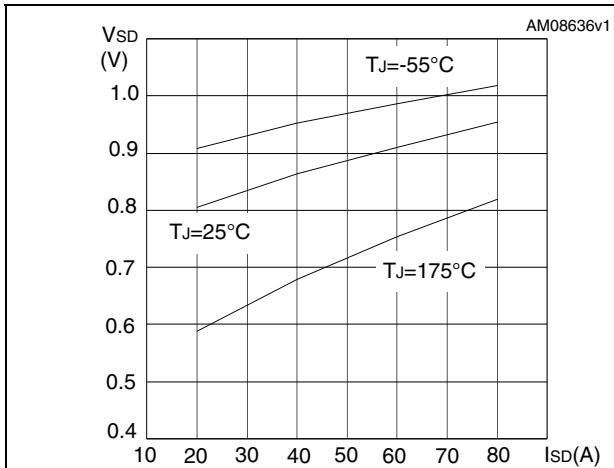


Figure 12. Source-drain diode forward characteristics



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and products status are available at: www.st.com. ECOPACK is an ST trademark.

Package mechanical data

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Table 9. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

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Package mechanical data

Figure 19. D²PAK footprint^(a)

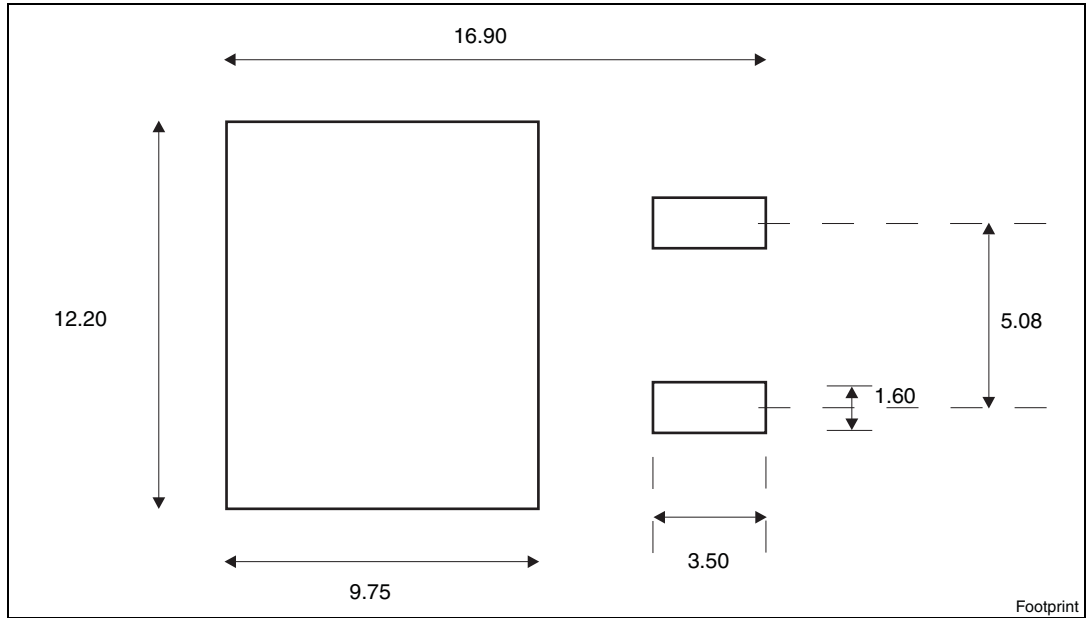
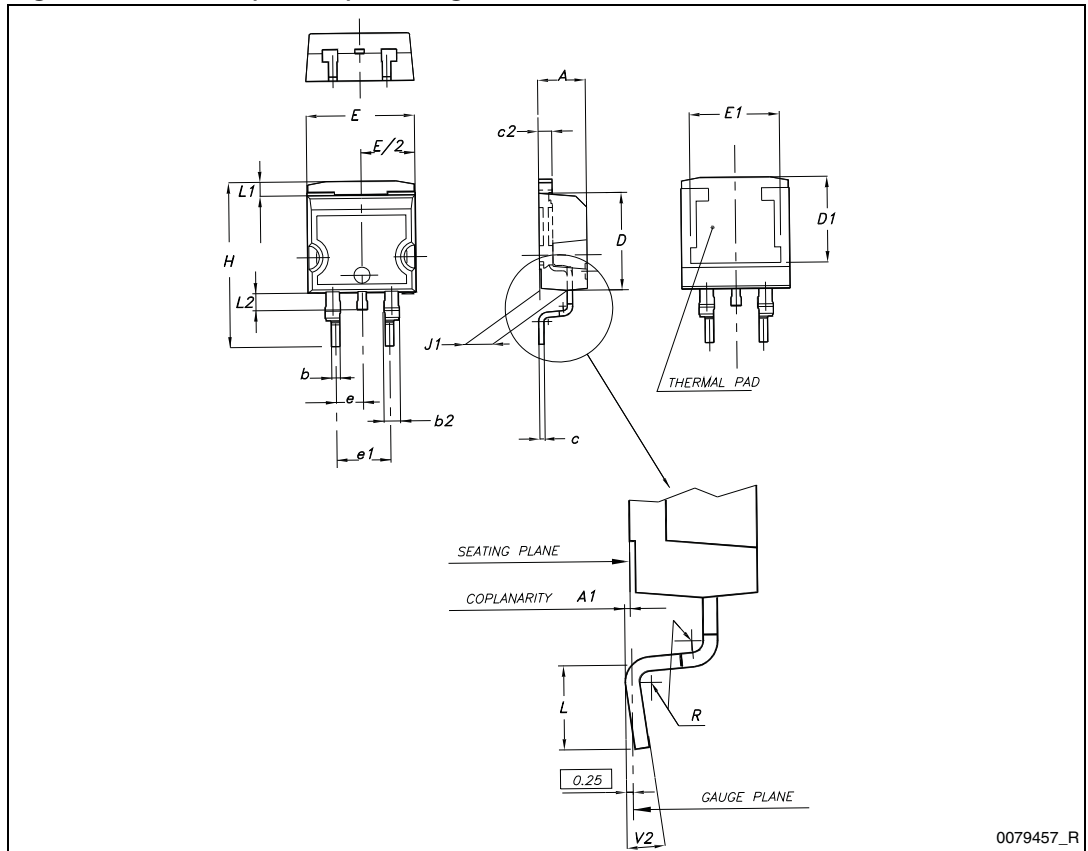


Figure 20. D²PAK (TO-263) drawing



a. All dimension are in millimeters

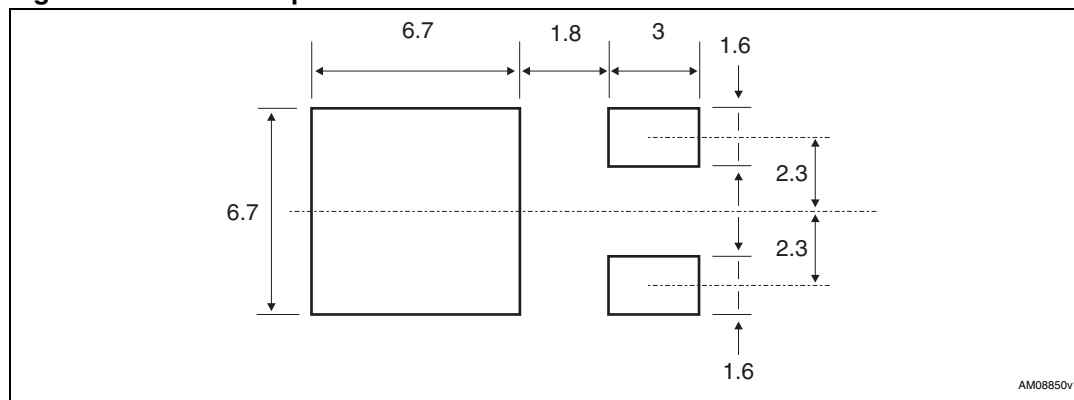
Package mechanical data

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Table 10. DPAK (TO-252) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		1.50
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°

Figure 21. DPAK footprint^(b)

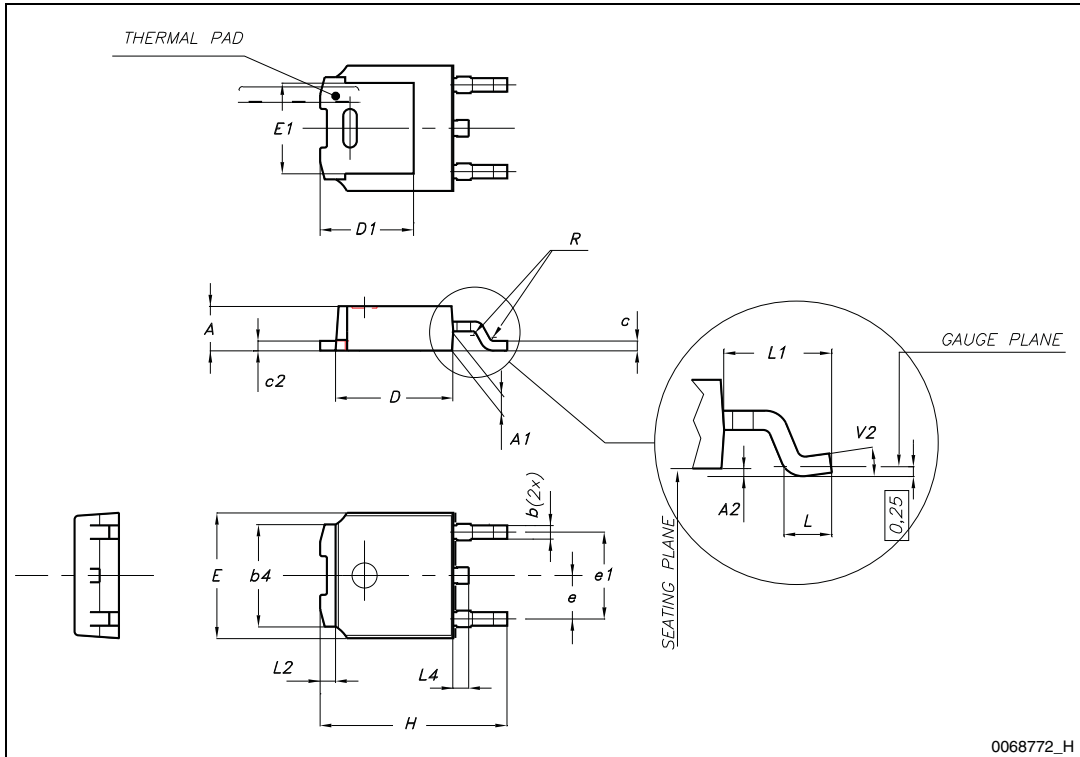


b. All dimension are in millimeters

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Package mechanical data

Figure 22. DPAK (TO-252) drawing



5 Packaging mechanical data

Table 11. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

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Packaging mechanical data

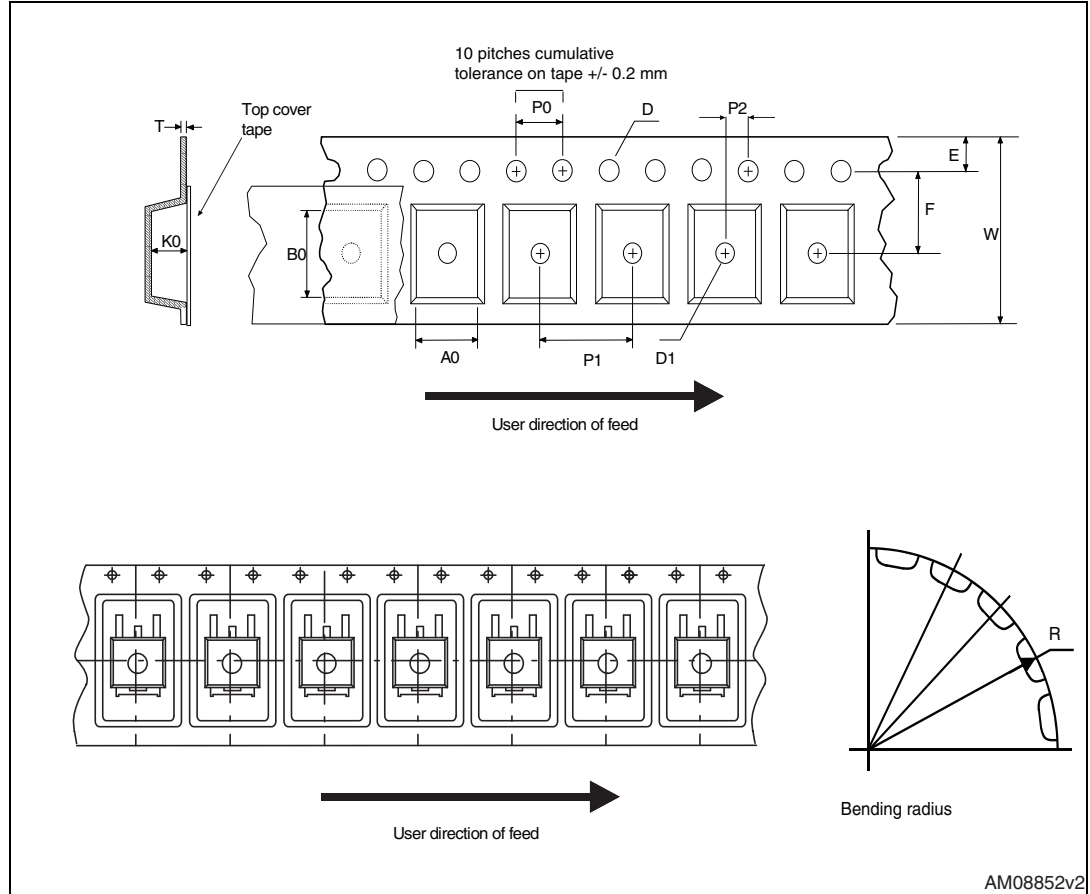
Table 12. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Packaging mechanical data

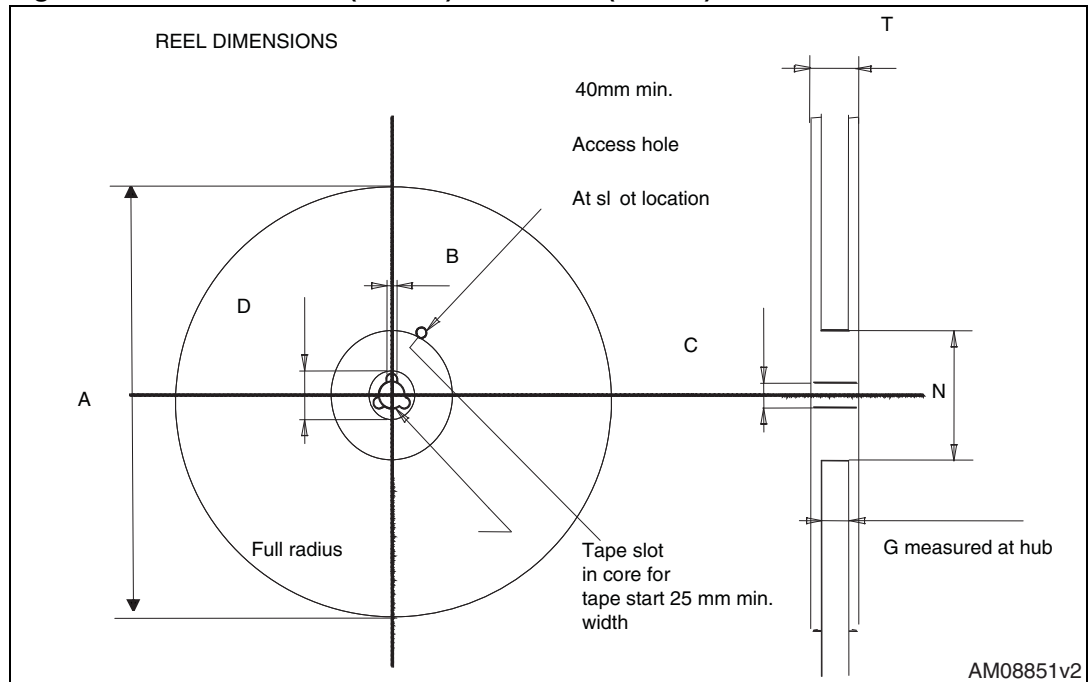
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Figure 23. Tape for DPAK (TO-252) and D²PAK (TO-263)



AM08852v2

Figure 24. Reel for DPAK (TO-252) and D²PAK (TO-263)



AM08851v2

6 Revision history

Table 13. Document revision history

Date	Revision	Changes
09-Feb-2010	1	First release
29-Oct-2010	2	Document status promoted from preliminary data to datasheet.
11-Nov-2010	3	Corrected $R_{DS(on)}$ value in Table 5: Static .
13-May-2011	4	Removed package and mechanical data: TO-220
17-May-2011	5	Description in cover page has been updated.

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